

NTE2559 (NPN) & NTE2560 (PNP) Silicon Complementary Transistors Darlington, Motor/Relay Driver

Absolute Maximum Ratings:

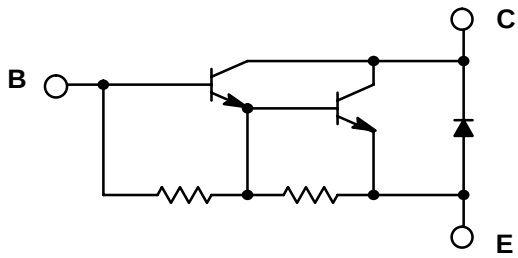
Collector–Base Voltage, V_{CBO}	120V
Collector–Emitter Voltage, V_{CEO}	120V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	16A
Pulsed	26A
Base Current, I_B	1A
Collector Dissipation ($T_{FL} = +25^\circ\text{C}$), P_D	3W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120\text{V}, I_E = 0$	–	–	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$	–	–	10	mA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, R_{BE} = \infty$	120	–	–	V
DC Current Gain	h_{FE}	$V_{CE} = 4\text{V}, I_C = 8\text{A}$	2000	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 8\text{A}, I_B = 16\text{mA}$	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 8\text{A}, I_B = 16\text{mA}$	–	–	2.5	V

Note 1. For NTE2560, the polarity is reversed.

NTE2559
(NPN)



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(PNP)

